

	Document ID	Issue Date	Pages	Title	Current OR	Current XRef	Inventor
1	US 5576566 A	19961119	10	Semiconductor trench capacitor cell having a buried strap	257/301	257/305	Kenney, Donald M.
2	US 5177576 A	19930105	22	Dynamic random access memory having trench capacitors and vertical transistors	257/71	257/302	Kimura, Shin'ichiro et al.
3	US 5065273 A	19911112	13	High capacity DRAM trench capacitor and methods of fabricating same	361/313	257/301; 438/243; 438/386	Rajeevakumar, Thekkemadathil V.
4	US 5930107 A	19990727	12	Dual trench capacitor	361/321.4	257/302; 361/321.5	Rajeevakumar, Thekkemadathil Velayudhan
5	US 4942554 A	19900717	6	Three-dimensional, one-transistor cell arrangement for dynamic semiconductor memories comprising trench capacitor and method for manufacturing same	365/149	257/304; 257/305	Kircher, Roland et al.
6	US 5843820 A	19981201	13	Method of fabricating a new dynamic random access memory (DRAM) cell having a buried horizontal trench capacitor	438/243	438/245; 438/388	Lu, Chih-Yuan
7	US 5521115 A	19960528	11	Method of making double grid substrate plate DRAM cell array	438/243	438/386	Park, Jong W. et al.
8	US 5563085 A	19961008	17	Method of manufacturing a semiconductor device	438/245	438/249	Kohyama, Yusuke
9	US 4988637 A	19910129	11	Method for fabricating a mesa transistor-trench capacitor memory cell structure	438/245		Dhong, Sang H. et al.